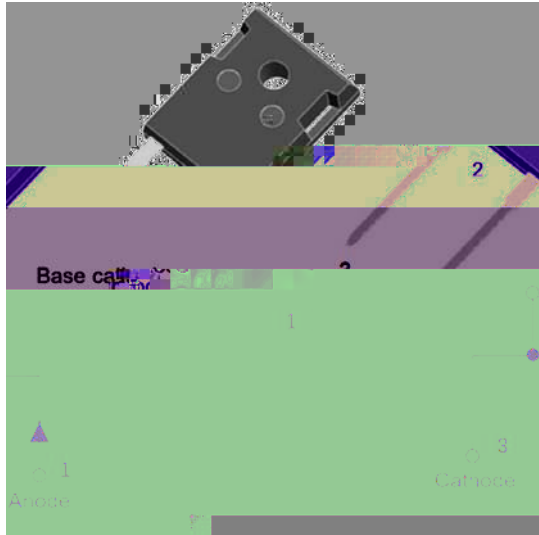


Silicon Carbide Schottky Diode

| | |
|-------------|------|
| V_{RRM} | 650V |
| I_F 135°C | 13A |
| Q_C | 60nC |



Features

- Positive temperature coefficient
 - Temperature-independent switching
 - Maximum working temperature at 175 °C
 - Unipolar devices and zero reverse recovery current
 - Zero forward recovery voltage
 - Essentially no switching losses
 - Reduction of heat sink requirements
 - High-frequency operation
 - Reduction of EMI
- o j .eł

Mechanical Data

- Package:** TO-247AC
- Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free
- Terminals:** Tin plated leads
- Polarity:** As marked

Maximum Rating

| | SYMBOL | UNIT | VALUE |
|--|----------------|------------------|-------------|
| Device marking code | | | D106510NQG2 |
| Reverse voltage (repetitive peak) @ $T_J=25^\circ\text{C}$ | V_{RRM} | V | 650 |
| Reverse voltage (Surge Peak) @ $T_J=25^\circ\text{C}$ | V_{RSM} | V | 650 |
| Reverse voltage (DC) @ $T_J=25^\circ\text{C}$ | V_{DC} | V | 650 |
| Continuous forward current @ $T_c=25^\circ\text{C}$ | I_F | A | 27 |
| Continuous forward current @ $T_c=135^\circ\text{C}$ | | | 13 |
| Continuous forward current @ $T_c=153^\circ\text{C}$ | | | 10 |
| Non-repetitive peak forward surge current @ $T_c=25^\circ\text{C}$, $t_p=10\text{ms}$, Half Sine Wave | I_{FSM} | A | 70 |
| Power Dissipation @ $T_c=25^\circ\text{C}$ | P_{TOT} | W | 126 |
| Power Dissipation @ $T_c=110^\circ\text{C}$ | | | 54 |
| i^2t Value @ $T_c=25^\circ\text{C}$, $t_p=10\text{ms}$ | i^2dt | A ² S | 24 |
| Operating junction and Storage temperature range | T_j, T_{stg} | °C | -55 to +175 |



Electrical Characteristics

| PARAMTETER | SYMBOL | UNIT | TEST CONDITIONS | Typ. | Max. |
|-------------------------|--------|---------|-----------------------------|------|------|
| Forward voltage drop | V_F | V | $I_F=10A, T_j=25^{\circ}C$ | | 1.55 |
| | | | $I_F=10A, T_j=.75^{\circ}C$ | .18 | - |
| Reverse leakage current | I_R | μA | $V_R=650V, T_j=25^{\circ}C$ | 0.5 | |

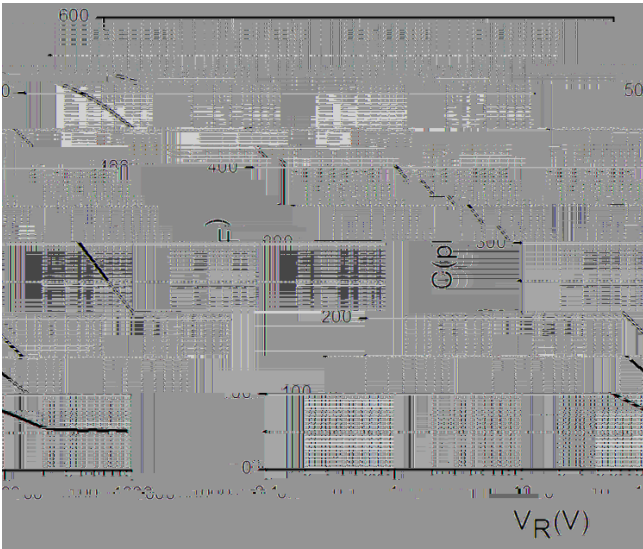


Figure 3. Capacitance vs. Reverse Voltage

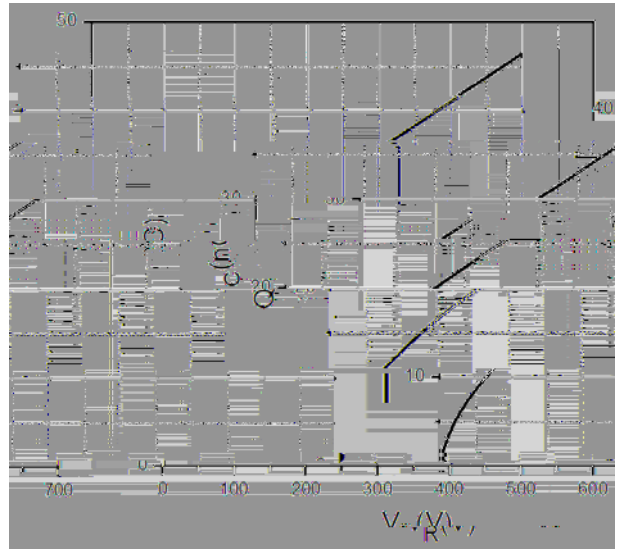


Figure 4. Total Capacitance Charge vs. Reverse Voltage

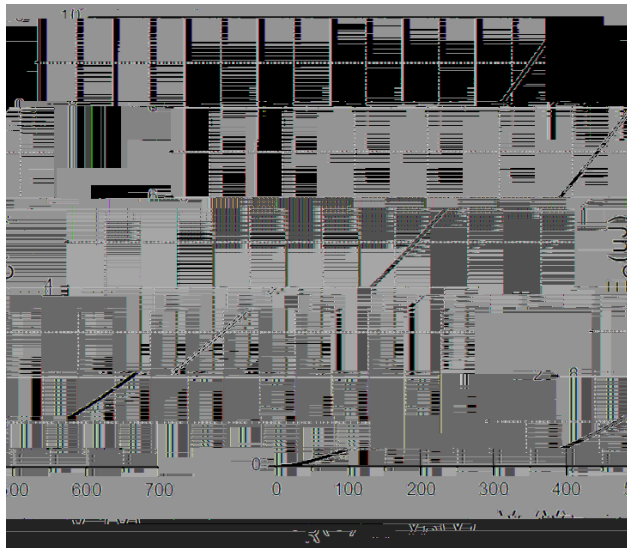


Figure 5. Capacitance Stored Energy

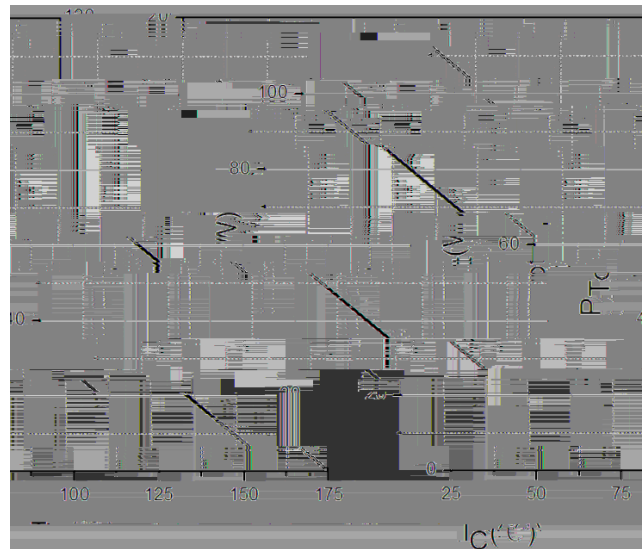


Figure 6. Power Derating

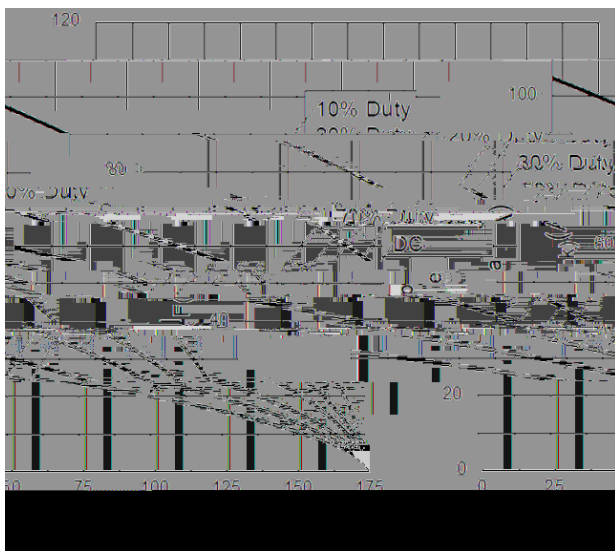


Figure 7. Current Derating

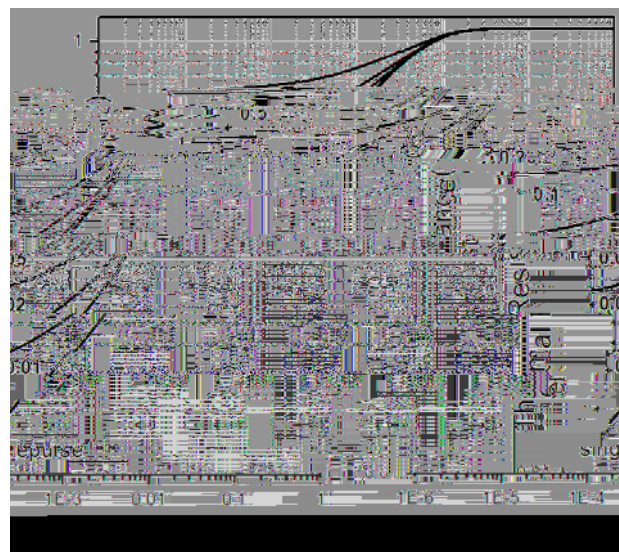


Figure 8. Transient Thermal Impedance



Outline Dimensions

| TO-247AC | | |
|----------|------|------|
| Dim | Min | Max |
| A | 4.80 | 5.20 |
| A1 | 2.21 | 2.61 |
| A2 | 1.85 | 2.15 |



Disclaimer

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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability an p